

650V Ultra Junction X2-Class Power MOSFETs

Ideal for Power Factor Correction (PFC) circuits and switching power supplies

I. MAIN FEATURES

- Low on-resistance $R_{DS(on)}$ and gate charge Q_g
- High power density
- dv/dt ruggedness
- Avalanche rated
- Low package inductance
- Space savings
- Easy mounting
- International standard packages

II. KEY TECHNOLOGY ADVANTAGES

Ultra-Junction Technology

These X2-Class Power MOSFETs are developed using a charge compensation principle and proprietary process technology; with significantly reduced on-state resistance and gate charge, they perform better than conventional superjunction devices, especially in hard switching applications.

Better Figure of Merit ($R_{DS(on)} \times Q_g$)

A low on-state resistance reduces the conduction losses. It also lowers the energy stored in the output capacitance, thereby minimizing the switching losses. A low gate charge results in higher efficiency at light loads as well as lower gate drive requirements. Efficiency, both at heavy and light loads, is optimized due to a better Figure of Merit.

dv/dt ruggedness and avalanche rating

The Ultra Junction MOSFETs are avalanche rated and display a superior dv/dt performance (50V/ns), exhibiting ruggedness against device failure caused by voltage spikes and turn-on of parasitic bipolar transistors inherent in the MOSFET structure.

III. TARGET APPLICATIONS

Designed for such applications as Power Factor Correction (PFC) circuits, switched-mode and resonant-mode power supplies, DC-DC converters, AC and DC motor drives, robotic and servo control, solar inverters, lighting control, these MOSFETs enable higher efficiency, along with high power density and cooler system performance.

IV. COMPETITIVE LANDSCAPE

The analyses were performed with devices retaining similar breakdown voltages and drain current ratings.

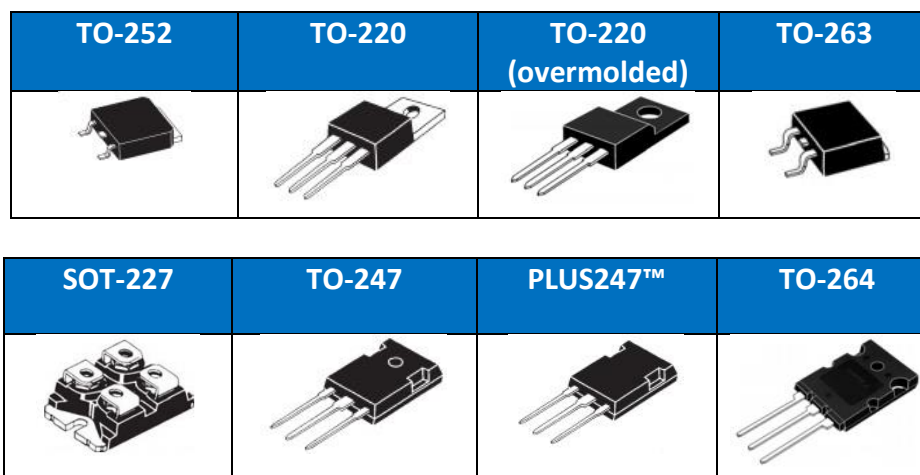
	IXTH34N65X2 (IXYS)	STW45N65M5 (STMicroelectronics)
Technology	Ultra Junction X2-Class	MDmesh™ M5
V _{DSS}	650V	650V
I _D @ T _j =25 °C	34A	35A
R _{DS(on)} (max)	105mΩ	78mΩ
Q _g (typ)	53nC	82nC
t _{rr} (typ)	400ns	392ns
Q _{RM} (typ)	3.5μC	7.4μC
dv/dt	50V/ns	50V/ns
R _{thJC} (max)	0.22 °C/W	0.6 °C/W
P _D	540W	210W
Package type	TO-247	TO-247

Table 1: IXTH34N65X2 vs. STW45N65M5

Compared to a similar ST Superjunction MOSFET, the IXYS part IXTH34N65X2 has a better (lower) Figure of Merit ($R_{DS(on)} \times Q_g$), along with a lower reverse recovery charge (Q_{RM}) and thermal resistance (R_{thJC}), enabling a higher system efficiency and cooler performance.

V. AVAILABLE PACKAGES

The 650V Ultra Junction Power MOSFETs are available in the following international standard size packages: TO-252, TO-220 (standard or overmolded), TO-263, SOT-227, TO-247, PLUS247™, and TO-264. Other standard and non-standard types may be manufactured upon request.



VI. PRICING

Part Number	V _{DSS} (V)	I _{D25} T _c =25°C (A)	R _{DS(on)} max. T _j =25°C (Ω)	Q _g typ. (nC)	Package Style	Pack Quantity	Average Selling Price (1 unit) (USD)
IXTP2N65X2	650	2	2.3	4.3	TO-220	50	\$1.92
IXTY2N65X2	650	2	2.3	4.3	TO-252	70	\$1.61
IXTA4N65X2	650	4	0.85	8.3	TO-263	50	\$2.05
IXTP4N65X2	650	4	0.85	8.3	TO-220	50	\$1.92
IXTP8N65X2M	650	4	0.55	12	TO-220 (overmolded)	50	\$2.29
IXTY4N65X2	650	4	0.85	8.3	TO-252	70	\$1.86
IXTA8N65X2	650	8	0.5	12	TO-263	50	\$2.48
IXTP8N65X2	650	8	0.5	12	TO-220	50	\$1.61
IXTY8N65X2	650	8	0.5	12	TO-252	70	\$2.23
IXTA12N65X2	650	12	0.3	17	TO-263	50	\$3.04
IXTH12N65X2	650	12	0.3	17	TO-247	30	\$3.70
IXTP12N65X2	650	12	0.3	17	TO-220	50	\$2.91
IXTH34N65X2	650	34	0.105	53	TO-247	30	\$5.60
IXTH48N65X2	650	48	0.068	77	TO-247	30	\$7.10
IXTH62N65X2	650	62	0.052	104	TO-247	30	\$8.40
IXTN102N65X2	650	76	0.03	152	SOT-227	10	\$23.84
IXTH80N65X2	650	80	0.04	144	TO-247	30	\$15.53
IXTK102N65X2	650	102	0.03	152	TO-264	25	\$13.77
IXTX102N65X2	650	102	0.03	152	PLUS247™	30	\$13.55
IXTK120N65X2	650	120	0.024	240	TO-264	25	\$17.78
IXTX120N65X2	650	120	0.024	240	PLUS247™	30	\$17.60